

P-channel Enhancement Mode Power MOSFET

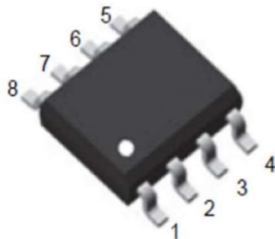
Features

- $V_{DS} = -40V$, $I_D = -13A$
 $R_{DS(ON)} < 12m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 14m\Omega @ V_{GS} = -4.5V$

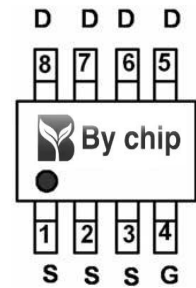
General Features

- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free and Green Available

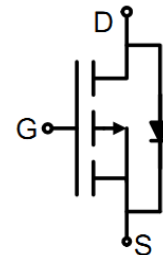
100% UIS TESTED!
 100% ΔV_{ds} TESTED!



SOP-8



pin assignment



Schematic diagram

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-13	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	-9	A
Pulsed Drain Current	I_{DM}	50	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance ,Junction-to-Ambient(Note 2)	$R_{\theta JA}$	50	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

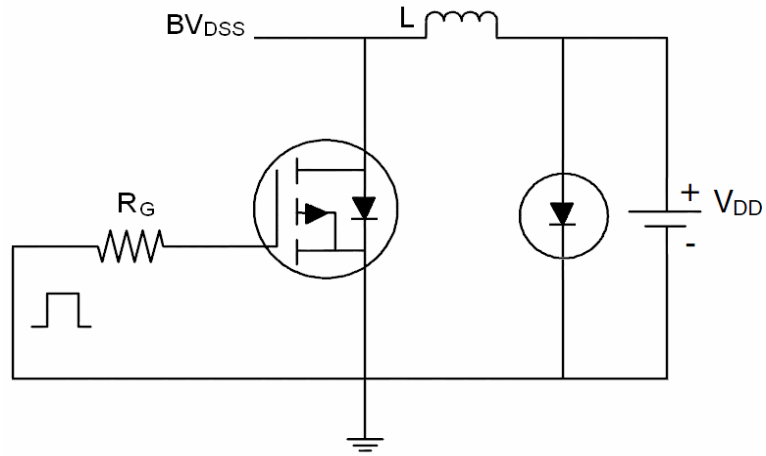
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-40V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0		-3.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-12A$	-		12	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-15V, I_D=-10A$	35	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=-20V, V_{GS}=0V,$ $F=1.0MHz$	-	2800	-	PF
Output Capacitance	C_{oss}		-	320	-	PF
Reverse Transfer Capacitance	C_{rss}		-	220	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, R_L=2\Omega$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	11	-	nS
Turn-on Rise Time	t_r		-	75	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	89	-	nS
Turn-Off Fall Time	t_f		-	35	-	nS
Total Gate Charge	Q_g	$V_{DS}=-20V, I_D=-12A,$ $V_{GS}=-10V$	-	40	-	nC
Gate-Source Charge	Q_{gs}		-	6	-	nC
Gate-Drain Charge	Q_{gd}		-	12	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-12A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-13	A

Notes:

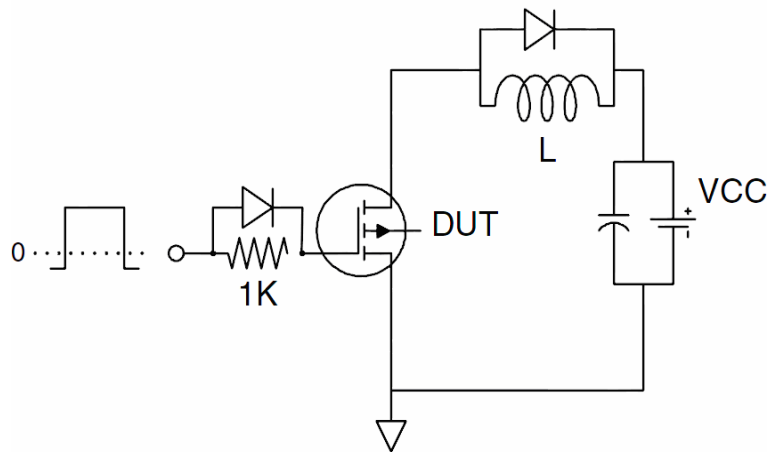
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

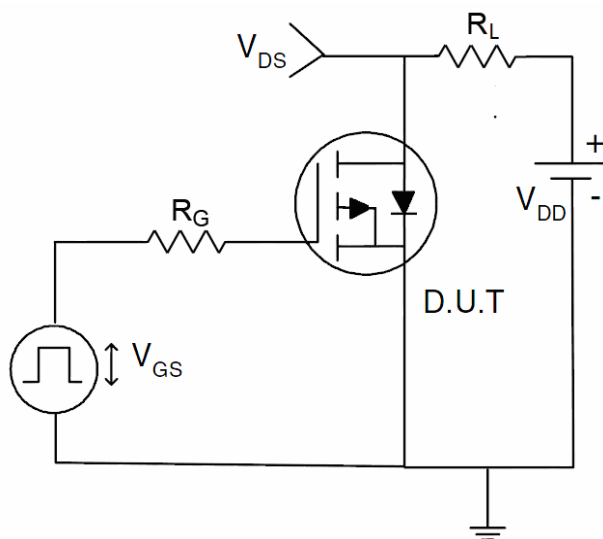
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

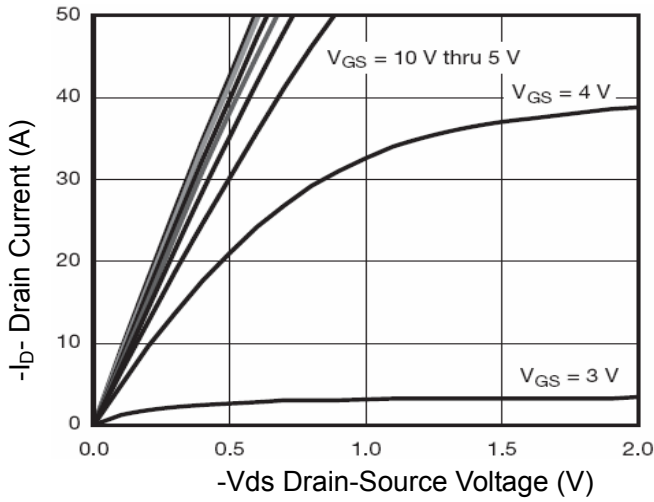


Figure 1 Output Characteristics

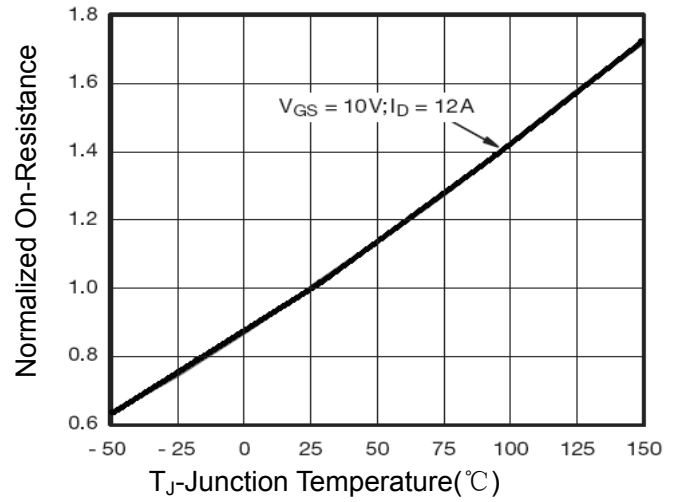


Figure 4 Rdson-Junction Temperature

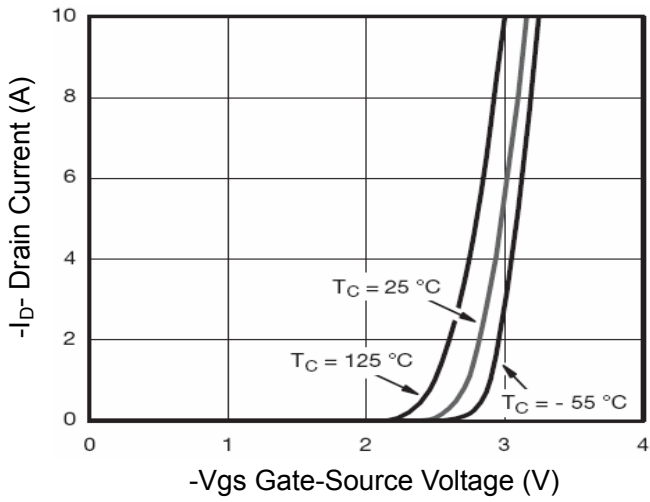


Figure 2 Transfer Characteristics

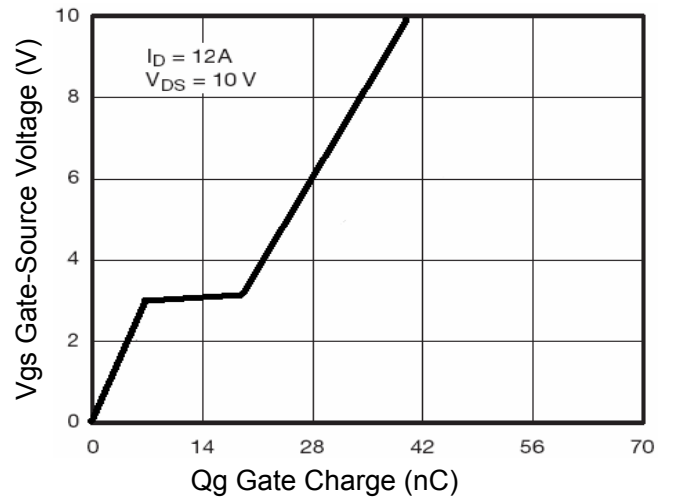


Figure 5 Gate Charge

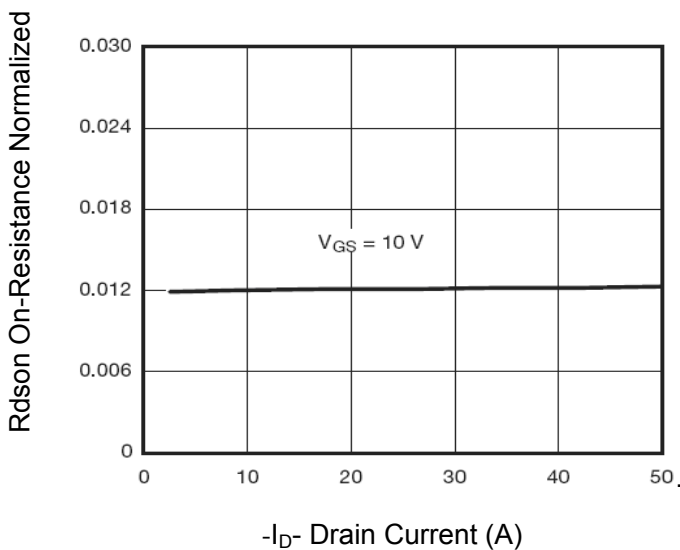


Figure 3 Rdson- Drain Current

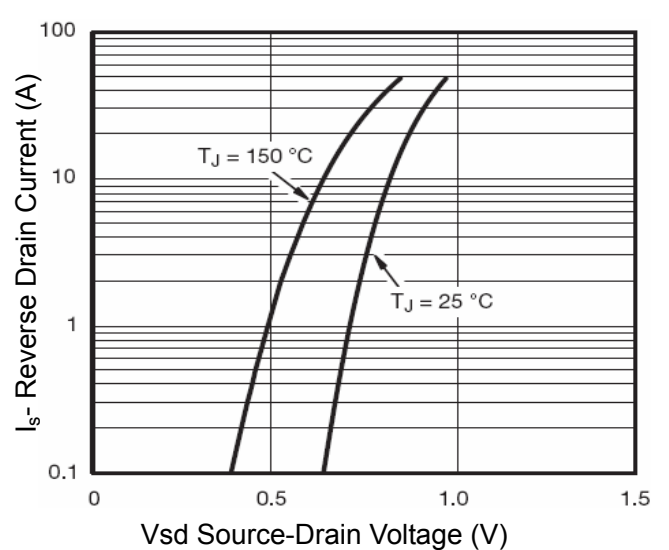


Figure 6 Source- Drain Diode Forward

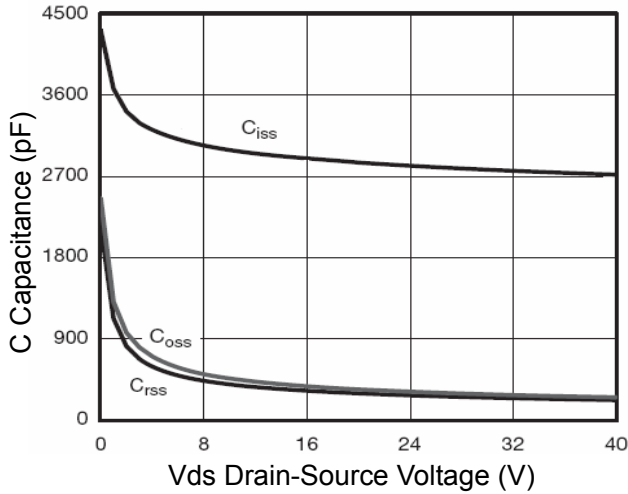


Figure 7 Capacitance vs Vds

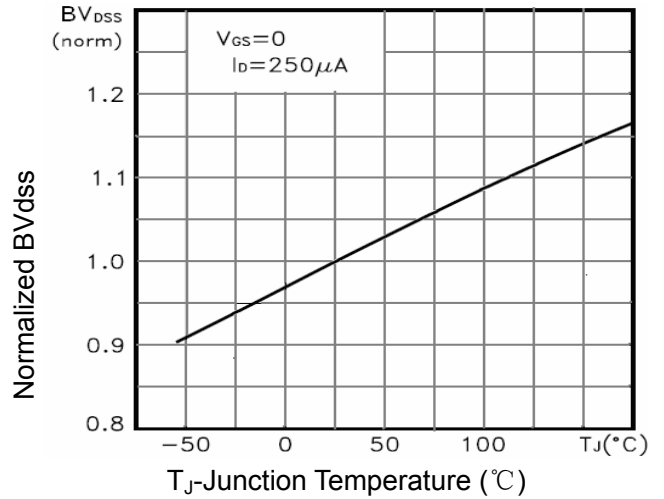


Figure 9 BV_{DSS} vs Junction Temperature

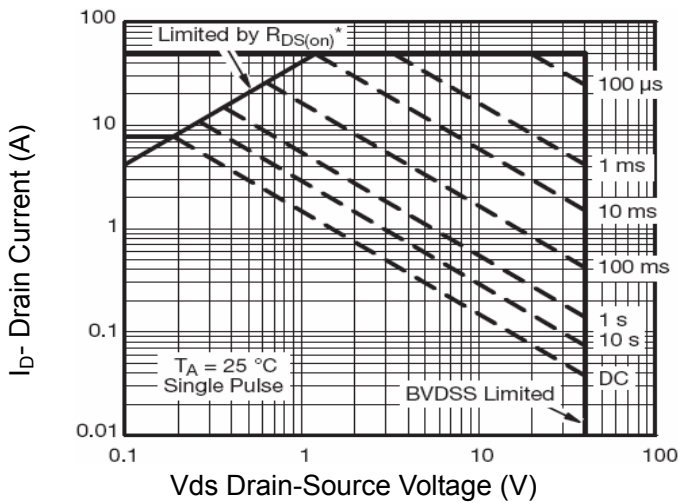


Figure 8 Safe Operation Area

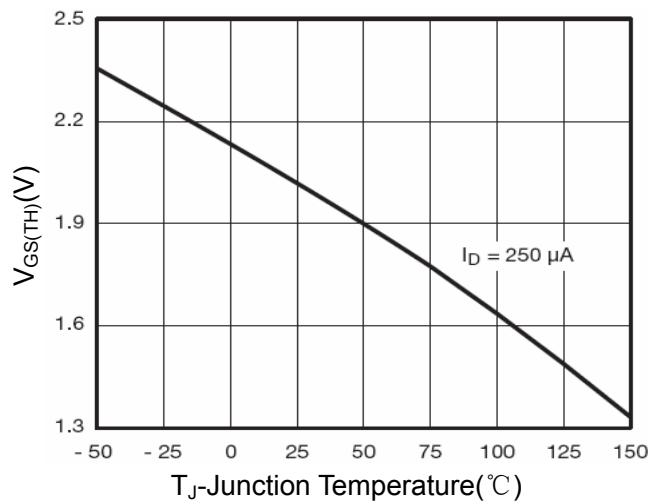


Figure 10 $V_{GS(th)}$ vs Junction Temperature

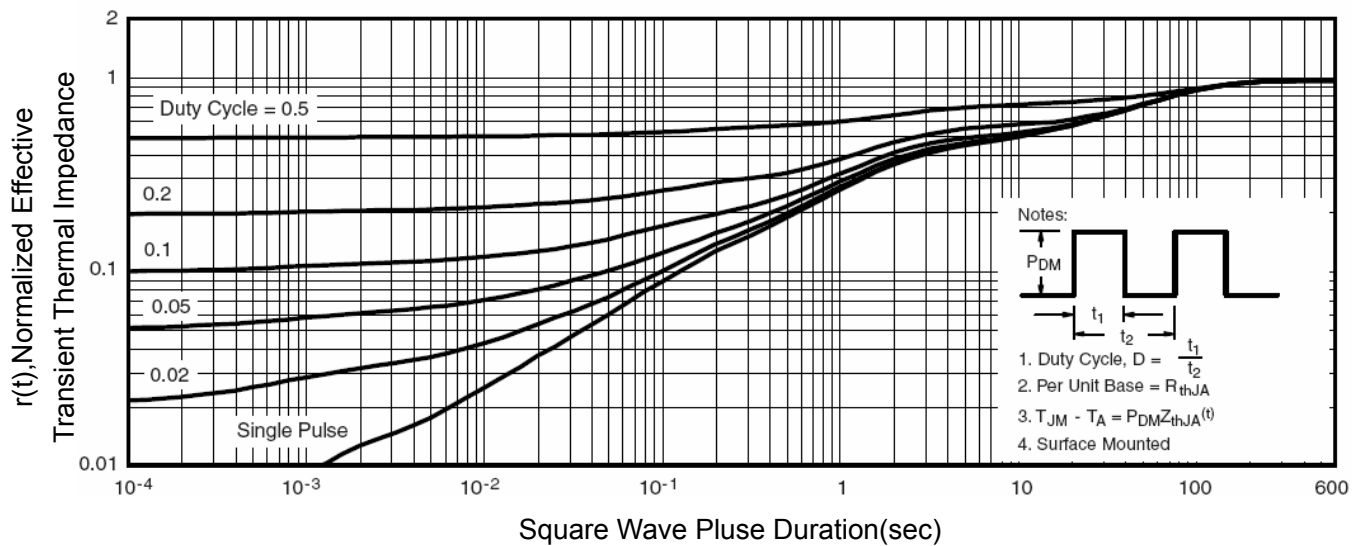


Figure 11 Normalized Maximum Transient Thermal Impedance